1994 GaAs REL Workshop Program
Sunday, October 16, Philadelphia

RELIABILITY OF O.25um GaAs MESFET MMIC PROCESS, RESULTS OF ACCELERATED LIFETESTS AND HYDROGEN EXPOSURE; M.J. Delaney and T.J. Wiltsey, Hughes Space and Communications Company, MW Chiang and K.K. Yu, Hughes Industrial Electronics Company

RELIABILITY OF GaAs PHEMT MMICs IN HYDROGEN AMBIENTS; S. Adams, J. MacDonald, W. Hu, A. Immodica, A. Reisinger, and F. Smith, Martin Marietta Laboratories of Syracuse

GaAs MMIC HYDROGEN DEGRADATION STUDY; K. Decker, Texas Instruments

ACCELERATED EFFECTS OF HYDROGEN ON GaAs MESFETS; W.J. Roesch, TriQuint Semiconductor, Inc.

ACTIVATION ENERGY & RATE OF HOT ELECTRON DEGRADATION OF GaAs MESFETs; Y.Tkachenko, and J. Hwang, Lehigh University, T. Harris & R.Grober, AT&T Bell Laboratories, & D. Hwang, Bellcore

HOT-ELECTRON EFFECTS IN VARIOUS POWERFET DESIGNS; F.A.Buotand, W.T.Anderson, Naval Research Laboratory, and C. Moglestue, Fraunhofer Institute of Applied Solid State Physics

FIELD DEPENDENT FAILURE MECHANISMS IN AlGaAs/GaAs HEMTs; K.A.Christianson and W.T. Anderson, Naval Research Laboratory, & C. Moglestue, Fraunhofer Institute of Applied Solid State Physics

MONTE CARLO SIMULATION OF OHMIC CONTACT DEGRADATION IN HEMTs; C. Mogiestue, Fraunhofer Institute of Applied Solid State Physics, and W.T. Anderson, Naval Research Laboratory

RELIABILITY STUDIES ON CARBON DOPED BASE AlGaAs/GaAs HBTS; S.J. Prasad and E. Hultine, Electronics Research Labs, Tektronix

DYNAMIC CURRENT STRESS EFFECTS ON MICROWAVE POWER HBTS; Y.C. Chou and G.P. Li, University of California, Y.H. Chang, National Yunlin Institute of Technology, C.S. Wu, P. Chu, C.K. Pao, D.C. Wang, and T.C. Cisco, Hughes Aircraft Company

RESOLVING BASE CURRENT INCRE4SE IN AlGaAs/GaAs HETEROJUNCTION BIPOLAR TRANSISTORS UNDER FORWARD CURRENT STRESS; H.Chang, National Yunlin Institute of Technology, Y.C.Chou, D.S. Quon, and G.P. Li, University of California

THERMAL ANALYSIS AND SENSITIVITY STUDY OF GaAs HBT DEVICES; J. Matthews and J. Nagurny, Martin Marietta Corporation, Government Electronic Systems

THERMAL STABILITY OF AlInAslGaInAslInP HETEROSTRUCTURES; N. Hayafuji, S. Takamiya, Y. Yamamoto, N. Yoshida, T. Sonoda, and S. Mitsui, Mitsubishi Electric Corporation

RELIABILITY OF METAL LAYERS ON GaAs MMICS; K.K. Yu, M.W. Chiang, and N. Kubota, GaAs Operations, Microelectronics Division, Hughes Aircraft Company

MATERIAL AND PROCESS RELIABILITY SURVEY USING ON-WAFER STEP-STRESSING; D.S. Whitefield, A.E. Geissberger, J.D. Jorgenson, D.C. Bartle, S.G. Munro, S.W. Walker, Alpha Industries

DEVELOPMENT OF ON-WAFER RELIABILITY TESTING TECHNIQUE; Y. Saito, R.Chan, J. Dowsing, and Y.Y. Tu, TRW Electronic Systems Group, and N. Koziarz and W. Koziarz, Rome Laboratory